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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	51
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l476rct6

Table 6. STM32L476xx peripherals interconnect matrix (continued)

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop 0 / Stop 1	Stop 2
GPIO	TIMx	External trigger	Y	Y	Y	Y	-	-
	LPTIMERx	External trigger	Y	Y	Y	Y	Y	Y ⁽¹⁾
	ADCx DACx DFSDM	Conversion external trigger	Y	Y	Y	Y	-	-

1. LPTIM1 only.

- Noise-wave generation
- Triangular-wave generation
- Dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- External triggers for conversion
- Sample and hold low-power mode, with internal or external capacitor

The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

3.17 Voltage reference buffer (VREFBUF)

The STM32L476xx devices embed an voltage reference buffer which can be used as voltage reference for ADCs, DACs and also as voltage reference for external components through the VREF+ pin.

The internal voltage reference buffer supports two voltages:

- 2.048 V
- 2.5 V.

An external voltage reference can be provided through the VREF+ pin when the internal voltage reference buffer is off.

The VREF+ pin is double-bonded with VDDA on some packages. In these packages the internal voltage reference buffer is not available.

3.18 Comparators (COMP)

The STM32L476xx devices embed two rail-to-rail comparators with programmable reference voltage (internal or external), hysteresis and speed (low speed for low-power) and with selectable output polarity.

The reference voltage can be one of the following:

- External I/O
- DAC output channels
- Internal reference voltage or submultiple (1/4, 1/2, 3/4).

All comparators can wake up from Stop mode, generate interrupts and breaks for the timers and can be also combined into a window comparator.

3.23 Random number generator (RNG)

All devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

3.24 Timers and watchdogs

The STM32L476 includes two advanced control timers, up to nine general-purpose timers, two basic timers, two low-power timers, two watchdog timers and a SysTick timer. The table below compares the features of the advanced control, general purpose and basic timers.

Table 10. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
Advanced control	TIM1, TIM8	16-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	3
General-purpose	TIM2, TIM5	32-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM3, TIM4	16-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	No
General-purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1
General-purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 and 65536	Yes	1	1
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

3.24.1 Advanced-control timer (TIM1, TIM8)

The advanced-control timer can each be seen as a three-phase PWM multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be seen as complete general-purpose timers. The 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

3.27 Universal synchronous/asynchronous receiver transmitter (USART)

The STM32L476xx devices have three embedded universal synchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4, UART5).

These interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. They provide hardware management of the CTS and RTS signals, and RS485 Driver Enable. They are able to communicate at speeds of up to 10Mbit/s.

USART1, USART2 and USART3 also provide Smart Card mode (ISO 7816 compliant) and SPI-like communication capability.

All USART have a clock domain independent from the CPU clock, allowing the USARTx (x=1,2,3,4,5) to wake up the MCU from Stop mode. The wake up events from Stop mode are programmable and can be:

- Start bit detection
- Any received data frame
- A specific programmed data frame

All USART interfaces can be served by the DMA controller.

Table 12. STM32L4x6 USART/UART/LPUART features

USART modes/features ⁽¹⁾	USART1	USART2	USART3	UART4	UART5	LPUART1
Hardware flow control for modem	X	X	X	X	X	X
Continuous communication using DMA	X	X	X	X	X	X
Multiprocessor communication	X	X	X	X	X	X
Synchronous mode	X	X	X	-	-	-
Smartcard mode	X	X	X	-	-	-
Single-wire half-duplex communication	X	X	X	X	X	X
IrDA SIR ENDEC block	X	X	X	X	X	-
LIN mode	X	X	X	X	X	-
Dual clock domain	X	X	X	X	X	X
Wakeup from Stop 0 / Stop 1 modes	X	X	X	X	X	X
Wakeup from Stop 2 mode	-	-	-	-	-	X
Receiver timeout interrupt	X	X	X	X	X	-
Modbus communication	X	X	X	X	X	-
Auto baud rate detection	X (4 modes)					-
Driver Enable	X	X	X	X	X	X
LPUART/USART data length	7, 8 and 9 bits					

1. X = supported.

3.36 Quad SPI memory interface (QUADSPI)

The Quad SPI is a specialized communication interface targeting single, dual or quad SPI flash memories. It can operate in any of the three following modes:

- Indirect mode: all the operations are performed using the QUADSPI registers
- Status polling mode: the external flash status register is periodically read and an interrupt can be generated in case of flag setting
- Memory-mapped mode: the external flash is memory mapped and is seen by the system as if it were an internal memory

The Quad SPI interface supports:

- Three functional modes: indirect, status-polling, and memory-mapped
- SDR and DDR support
- Fully programmable opcode for both indirect and memory mapped mode
- Fully programmable frame format for both indirect and memory mapped mode
- Each of the 5 following phases can be configured independently (enable, length, single/dual/quad communication)
 - Instruction phase
 - Address phase
 - Alternate bytes phase
 - Dummy cycles phase
 - Data phase
- Integrated FIFO for reception and transmission
- 8, 16, and 32-bit data accesses are allowed
- DMA channel for indirect mode operations
- Programmable masking for external flash flag management
- Timeout management
- Interrupt generation on FIFO threshold, timeout, status match, operation complete, and access error

Table 15. STM32L476xxSTM32L476xx pin definitions (continued)

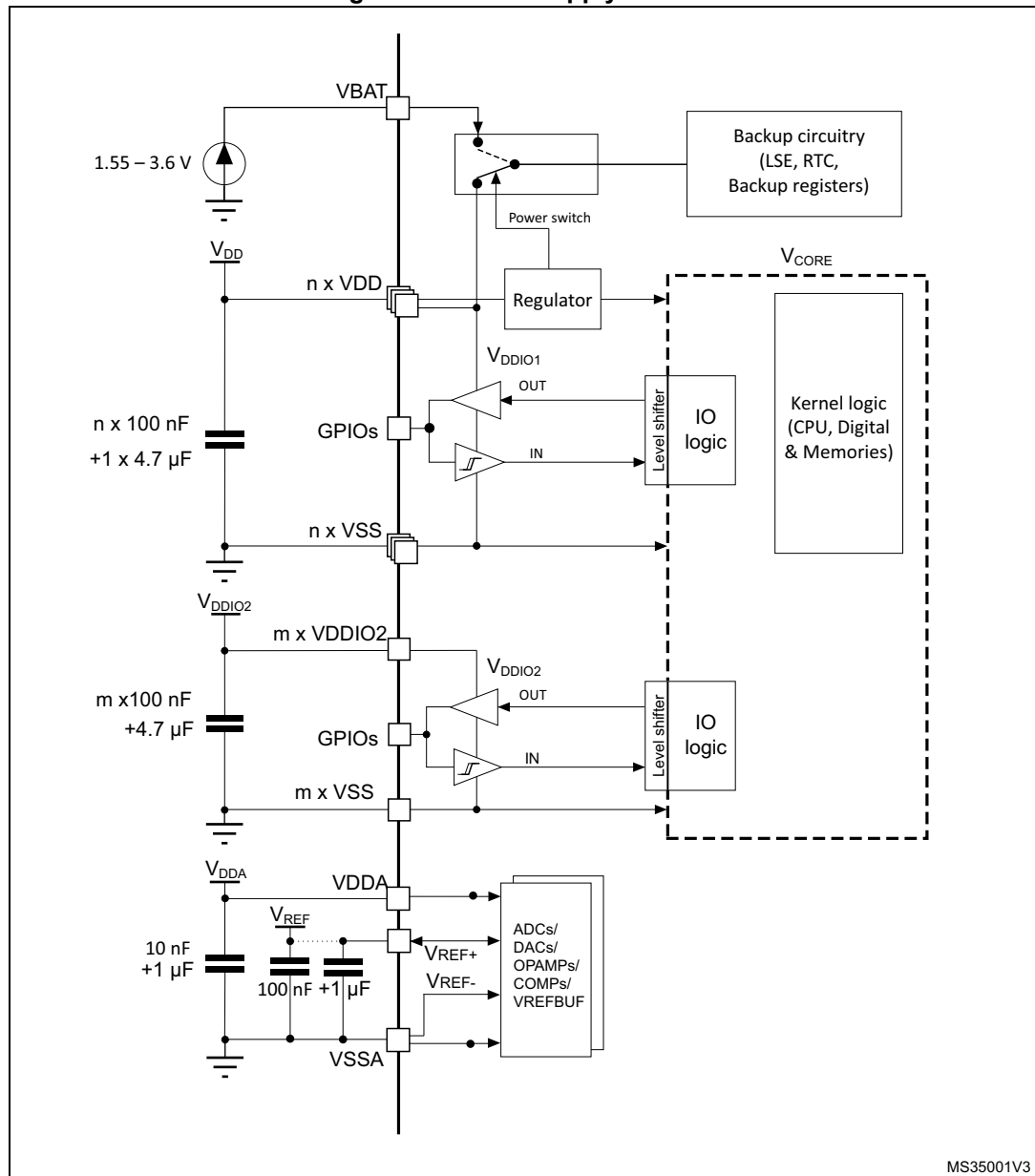
Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP72	WLCSP81	LQFP100	UFBGA132	LQFP144					Alternate functions	Additional functions
45	C1	C1	71	A12	104	PA12	I/O	FT_u	-	TIM1_ETR, USART1_RTS_DE, CAN1_TX, OTG_FS_DP, EVENTOUT	-
46	C2	C2	72	A11	105	PA13 (JTMS-SWDIO)	I/O	FT	(3)	JTMS-SWDIO, IR_OUT, OTG_FS_NOE, EVENTOUT	-
47	B1	B1	-	-	-	VSS	S	-	-	-	-
48	A1	A1	73	C11	106	VDDUSB	S	-	-	-	-
-	-	-	74	F11	107	VSS	S	-	-	-	-
-	-	-	75	G11	108	VDD	S	-	-	-	-
49	B2	B2	76	A10	109	PA14 (JTCK-SWCLK)	I/O	FT	(3)	JTCK-SWCLK, EVENTOUT	-
50	A2	A2	77	A9	110	PA15 (JTDI)	I/O	FT_I	(3)	JTDI, TIM2_CH1, TIM2_ETR, SPI1_NSS, SPI3_NSS, UART4_RTS_DE, TSC_G3_IO1, LCD_SEG17, SAI2_FS_B, EVENTOUT	-
51	D3	D3	78	B11	111	PC10	I/O	FT_I	-	SPI3_SCK, USART3_TX, UART4_TX, TSC_G3_IO2, LCD_COM4/LCD_SEG28/ LCD_SEG40, SDMMC1_D2, SAI2_SCK_B, EVENTOUT	-
52	C3	C3	79	C10	112	PC11	I/O	FT_I	-	SPI3_MISO, USART3_RX, UART4_RX, TSC_G3_IO3, LCD_COM5/LCD_SEG29/ LCD_SEG41, SDMMC1_D3, SAI2_MCLK_B, EVENTOUT	-
53	B3	B3	80	B10	113	PC12	I/O	FT_I	-	SPI3_MOSI, USART3_CK, UART5_TX, TSC_G3_IO4, LCD_COM6/LCD_SEG30/ LCD_SEG42, SDMMC1_CK, SAI2_SD_B, EVENTOUT	-
-	-	-	81	C9	114	PD0	I/O	FT	-	SPI2_NSS, DFSDM_DATIN7, CAN1_RX, FMC_D2, EVENTOUT	-

Table 16. Alternate function AF0 to AF7 (for AF8 to AF15 see [Table 17](#)) (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		SYS_AF	TIM1/TIM2/ TIM5/TIM8/ LPTIM1	TIM1/TIM2/ TIM3/TIM4/ TIM5	TIM8	I2C1/I2C2/I2C3	SPI1/SPI2	SPI3/DFSDM	USART1/ USART2/ USART3
Port B	PB0	-	TIM1_CH2N	TIM3_CH3	TIM8_CH2N	-	-	-	USART3_CK
	PB1	-	TIM1_CH3N	TIM3_CH4	TIM8_CH3N	-	-	DFSDM_DATIN0	USART3_RTS_ DE
	PB2	RTC_OUT	LPTIM1_OUT	-	-	I2C3_SMBA	-	DFSDM_CKIN0	-
	PB3	JTDO- TRACESWO	TIM2_CH2	-	-	-	SPI1_SCK	SPI3_SCK	USART1_RTS_ DE
	PB4	NJTRST	-	TIM3_CH1	-	-	SPI1_MISO	SPI3_MISO	USART1_CTS
	PB5	-	LPTIM1_IN1	TIM3_CH2	-	I2C1_SMBA	SPI1_MOSI	SPI3_MOSI	USART1_CK
	PB6	-	LPTIM1_ETR	TIM4_CH1	TIM8_BKIN2	I2C1_SCL	-	DFSDM_DATIN5	USART1_TX
	PB7	-	LPTIM1_IN2	TIM4_CH2	TIM8_BKIN	I2C1_SDA	-	DFSDM_CKIN5	USART1_RX
	PB8	-	-	TIM4_CH3	-	I2C1_SCL	-	DFSDM_DATIN6	-
	PB9	-	IR_OUT	TIM4_CH4	-	I2C1_SDA	SPI2_NSS	DFSDM_CKIN6	-
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK	DFSDM_DATIN7	USART3_TX
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	DFSDM_CKIN7	USART3_RX
	PB12	-	TIM1_BKIN	-	TIM1_BKIN_ COMP2	I2C2_SMBA	SPI2_NSS	DFSDM_DATIN1	USART3_CK
	PB13	-	TIM1_CH1N	-	-	I2C2_SCL	SPI2_SCK	DFSDM_CKIN1	USART3_CTS
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	I2C2_SDA	SPI2_MISO	DFSDM_DATIN2	USART3_RTS_ DE
	PB15	RTC_REFIN	TIM1_CH3N	-	TIM8_CH3N	-	SPI2_MOSI	DFSDM_CKIN2	-

6.1.6 Power supply scheme

Figure 13. Power supply scheme



MS35001V3

Caution: Each power supply pair (V_{DD}/V_{SS} , V_{DDA}/V_{SSA} etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.



Table 33. Current consumption in Low-power sleep modes, Flash in power-down

Symbol	Parameter	Conditions			TYP					MAX ⁽¹⁾					Unit
		-	Voltage scaling	f _{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (LPSleep)	Supply current in low-power sleep mode	f _{HCLK} = f _{MSI} all peripherals disable			2 MHz	81	110	217	395	754	115	182	375	750	1500
					1 MHz	50	78	185	362	720	80	149	342	717	1456
					400 kHz	28	57	163	340	698	60	122	314	689	1429
					100 kHz	18	47	155	332	686	50	114	313	688	1438

1. Guaranteed by characterization results, unless otherwise specified.

Table 34. Current consumption in Stop 2 mode

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (Stop 2)	Supply current in Stop 2 mode, RTC disabled	LCD disabled	1.8 V	1.14	3.77	14.7	34.7	77	2.7	9	37	87	193	μA
			2.4 V	1.15	3.86	15	35.5	79.1	2.7	10	38	89	198	
			3 V	1.18	3.97	15.4	36.4	81.3	2.8	10	39	91	203	
			3.6 V	1.26	4.11	16	38	85.1	3.0	10	40	95 ⁽²⁾	213	
		LCD enabled ⁽³⁾ clocked by LSI	1.8 V	1.43	3.98	15	35	77.3	3.2	10	38	88	193	
			2.4 V	1.49	4.07	15.3	35.8	79.4	3.2	10	38	90	199	
			3 V	1.54	4.24	15.7	36.7	81.6	3.3	11	39	92	204	
			3.6 V	1.75	4.47	16.1	38.3	85.4	3.5	11	40	96	214	

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in [Table 58: I/O static characteristics](#).

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see [Table 40: Peripheral current consumption](#)), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DDIOx} is the I/O supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO.

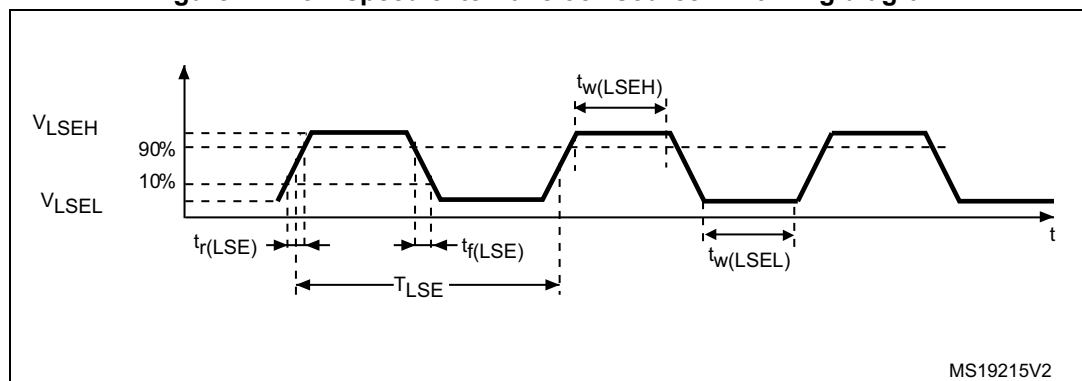
The external clock signal has to respect the I/O characteristics in [Section 6.3.14](#). However, the recommended clock input waveform is shown in [Figure 17](#).

Table 44. Low-speed external user clock characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	-	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage	-	$0.7 V_{DDIOx}$	-	V_{DDIOx}	V
V_{LSEL}	OSC32_IN input pin low level voltage	-	V_{SS}	-	$0.3 V_{DDIOx}$	
$t_{w(LSEH)}$ $t_{w(LSEL)}$	OSC32_IN high or low time	-	250	-	-	ns

1. Guaranteed by design.

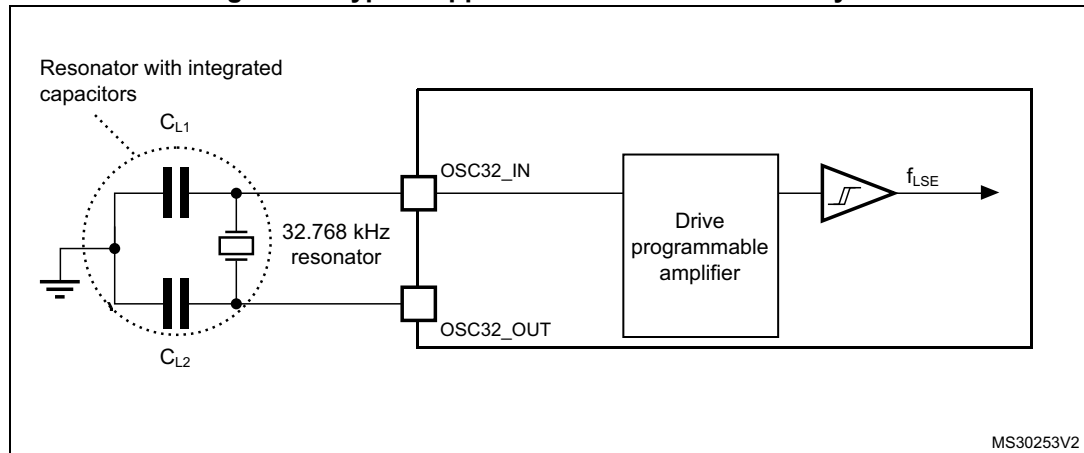
Figure 17. Low-speed external clock source AC timing diagram



1. Guaranteed by design.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 19. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between $OSC32_IN$ and $OSC32_OUT$ and it is forbidden to add one.

Table 48. MSI oscillator characteristics⁽¹⁾ (continued)

Symbol	Parameter	Conditions			Min	Typ	Max	Unit	
$\Delta V_{DD}(MSI)^{(2)}$	MSI oscillator frequency drift over V_{DD} (reference is 3 V)	MSI mode	Range 0 to 3	$V_{DD}=1.62$ V to 3.6 V	-1.2	-	0.5	%	
				$V_{DD}=2.4$ V to 3.6 V	-0.5	-			
			Range 4 to 7	$V_{DD}=1.62$ V to 3.6 V	-2.5	-	0.7		
				$V_{DD}=2.4$ V to 3.6 V	-0.8	-			
			Range 8 to 11	$V_{DD}=1.62$ V to 3.6 V	-5	-	1		
				$V_{DD}=2.4$ V to 3.6 V	-1.6	-			
$\Delta F_{SAMPLING}(MSI)^{(2)(6)}$	Frequency variation in sampling mode ⁽³⁾	MSI mode	$T_A= -40$ to 85 °C		-	1	2	%	
			$T_A= -40$ to 125 °C		-	2	4		
P_USB Jitter(MSI) ⁽⁶⁾	Period jitter for USB clock ⁽⁴⁾	PLL mode Range 11	for next transition	-	-	-	3.458	ns	
			for paired transition	-	-	-	3.916		
MT_USB Jitter(MSI) ⁽⁶⁾	Medium term jitter for USB clock ⁽⁵⁾	PLL mode Range 11	for next transition	-	-	-	2	ns	
			for paired transition	-	-	-	1		
CC jitter(MSI) ⁽⁶⁾	RMS cycle-to-cycle jitter	PLL mode Range 11			-	-	60	-	ps
P jitter(MSI) ⁽⁶⁾	RMS Period jitter	PLL mode Range 11			-	-	50	-	ps
$t_{SU}(MSI)^{(6)}$	MSI oscillator start-up time	Range 0		-	-	10	20	us	
		Range 1		-	-	5	10		
		Range 2		-	-	4	8		
		Range 3		-	-	3	7		
		Range 4 to 7		-	-	3	6		
		Range 8 to 11		-	-	2.5	6		
$t_{STAB}(MSI)^{(6)}$	MSI oscillator stabilization time	PLL mode Range 11	10 % of final frequency	-	-	0.25	0.5	ms	
			5 % of final frequency	-	-	0.5	1.25		
			1 % of final frequency	-	-	-	2.5		

6.3.10 Flash memory characteristics

Table 51. Flash memory characteristics⁽¹⁾

Symbol	Parameter	Conditions	Typ	Max	Unit
t_{prog}	64-bit programming time	-	81.69	90.76	μs
$t_{\text{prog_row}}$	one row (32 double word) programming time	normal programming	2.61	2.90	ms
		fast programming	1.91	2.12	
$t_{\text{prog_page}}$	one page (2 Kbyte) programming time	normal programming	20.91	23.24	
		fast programming	15.29	16.98	
t_{ERASE}	Page (2 KB) erase time	-	22.02	24.47	
$t_{\text{prog_bank}}$	one bank (512 Kbyte) programming time	normal programming	5.35	5.95	s
		fast programming	3.91	4.35	
t_{ME}	Mass erase time (one or two banks)	-	22.13	24.59	ms
I_{DD}	Average consumption from V_{DD}	Write mode	3.4	-	mA
		Erase mode	3.4	-	
	Maximum current (peak)	Write mode	7 (for 2 μs)	-	
		Erase mode	7 (for 41 μs)	-	

1. Guaranteed by design.

Table 52. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min ⁽¹⁾	Unit
N_{END}	Endurance	$T_{\text{A}} = -40$ to $+105$ °C	10	kcycles
t_{RET}	Data retention	1 kcycle ⁽²⁾ at $T_{\text{A}} = 85$ °C	30	Years
		1 kcycle ⁽²⁾ at $T_{\text{A}} = 105$ °C	15	
		1 kcycle ⁽²⁾ at $T_{\text{A}} = 125$ °C	7	
		10 kcycles ⁽²⁾ at $T_{\text{A}} = 55$ °C	30	
		10 kcycles ⁽²⁾ at $T_{\text{A}} = 85$ °C	15	
		10 kcycles ⁽²⁾ at $T_{\text{A}} = 105$ °C	10	

1. Guaranteed by characterization results.

2. Cycling performed over the whole temperature range.

Table 68. ADC accuracy - limited test conditions 4⁽¹⁾(2)(3) (continued)

Sym- bol	Parameter	Conditions ⁽⁴⁾			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency \leq 26 MHz, $1.65\text{ V} \leq V_{DDA} = V_{REF+} \leq 3.6\text{ V}$, Voltage scaling Range 2	Single ended	Fast channel (max speed)	-	-71	-69	dB
				Slow channel (max speed)	-	-71	-69	
			Differential	Fast channel (max speed)	-	-73	-72	
				Slow channel (max speed)	-	-73	-72	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when $V_{DDA} < 2.4\text{ V}$ (BOOSTEN = 1 in the SYSCFG_CFGR1 when $V_{DDA} < 2.4\text{ V}$). It is disable when $V_{DDA} \geq 2.4\text{ V}$. No oversampling.

SAI characteristics

Unless otherwise specified, the parameters given in [Table 86](#) for SAI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 22: General operating conditions](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 10$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5 \times V_{DD}$

Refer to [Section 6.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CK,SD,FS).

Table 86. SAI characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCLK}	SAI Main clock output	-	-	50	MHz
f_{CK}	SAI clock frequency ⁽²⁾	Master transmitter $2.7 \leq V_{DD} \leq 3.6$ Voltage Range 1	-	18.5	MHz
		Master transmitter $1.71 \leq V_{DD} \leq 3.6$ Voltage Range 1	-	12.5	
		Master receiver Voltage Range 1	-	25	
		Slave transmitter $2.7 \leq V_{DD} \leq 3.6$ Voltage Range 1	-	22.5	
		Slave transmitter $1.71 \leq V_{DD} \leq 3.6$ Voltage Range 1	-	14.5	
		Slave receiver Voltage Range 1	-	25	
		Voltage Range 2	-	12.5	
$t_{V(FS)}$	FS valid time	Master mode $2.7 \leq V_{DD} \leq 3.6$	-	22	ns
		Master mode $1.71 \leq V_{DD} \leq 3.6$	-	40	
$t_{h(FS)}$	FS hold time	Master mode	10	-	ns
$t_{su(FS)}$	FS setup time	Slave mode	1	-	ns
$t_{h(FS)}$	FS hold time	Slave mode	2	-	ns
$t_{su(SD_A_MR)}$	Data input setup time	Master receiver	2.5	-	ns
$t_{su(SD_B_SR)}$		Slave receiver	3	-	
$t_{h(SD_A_MR)}$	Data input hold time	Master receiver	8	-	ns
$t_{h(SD_B_SR)}$		Slave receiver	4	-	

Table 99. Synchronous multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}-1$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low ($x=0..2$)	-	2	
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high ($x=0..2$)	$T_{HCLK}+0.5$	-	
$t_{d(CLKL-NADV_L)}$	FMC_CLK low to FMC_NADV low	-	2.5	
$t_{d(CLKL-NADV_H)}$	FMC_CLK low to FMC_NADV high	1	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid ($x=16..25$)	-	3.5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid ($x=16..25$)	T_{HCLK}	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	2	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}+1$	-	
$t_{d(CLKL-ADV)}$	FMC_CLK low to FMC_AD[15:0] valid	-	4	
$t_{d(CLKL-ADIV)}$	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
$t_{d(CLKL-DATA)}$	FMC_A/D[15:0] valid data after FMC_CLK low	-	5.5	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	-	2.5	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}+1$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	0	-	
$t_h(CLKH-NWAIT)$	FMC_NWAIT valid after FMC_CLK high	4	-	

1. CL = 30 pF.

2. Guaranteed by characterization results.

Table 101. Synchronous non-multiplexed PSRAM write timings⁽¹⁾⁽²⁾

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FMC_CLK period	$2T_{HCLK}-0.5$	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low ($x=0..2$)	-	2	
$t_{d(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high ($x=0..2$)	$T_{HCLK}+0.5$	-	
$t_{d(CLKL-NADV_L)}$	FMC_CLK low to FMC_NADV low	-	2	
$t_{d(CLKL-NADV_H)}$	FMC_CLK low to FMC_NADV high	2.5	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid ($x=16..25$)	-	5	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid ($x=16..25$)	$T_{HCLK}-1$	-	
$t_{d(CLKL-NWE_L)}$	FMC_CLK low to FMC_NWE low	-	2	
$t_{d(CLKH-NWE_H)}$	FMC_CLK high to FMC_NWE high	$T_{HCLK}-1$	-	
$t_{d(CLKL-Data)}$	FMC_D[15:0] valid data after FMC_CLK low	-	4.5	
$t_{d(CLKL-NBL_L)}$	FMC_CLK low to FMC_NBL low	1.5	-	
$t_{d(CLKH-NBL_H)}$	FMC_CLK high to FMC_NBL high	$T_{HCLK}+1$	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	0	-	
$t_h(CLKH-NWAIT)$	FMC_NWAIT valid after FMC_CLK high	4	-	

1. CL = 30 pF.

2. Guaranteed by characterization results.

NAND controller waveforms and timings

[Figure 45](#) through [Figure 48](#) represent synchronous waveforms, and [Table 102](#) and [Table 103](#) provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x02
- COM.FMC_WaitSetupTime = 0x03
- COM.FMC_HoldSetupTime = 0x02
- COM.FMC_HiZSetupTime = 0x03
- ATT.FMC_SetupTime = 0x01
- ATT.FMC_WaitSetupTime = 0x03
- ATT.FMC_HoldSetupTime = 0x02
- ATT.FMC_HiZSetupTime = 0x03
- Bank = FMC_Bank_NAND
- MemoryDataWidth = FMC_MemoryDataWidth_16b
- ECC = FMC_ECC_Enable
- ECCPageSize = FMC_ECCPageSize_512Bytes
- TCLRSetupTime = 0
- TARSetupTime = 0

In all timing tables, the T_{HCLK} is the HCLK clock period.

Figure 55. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline

1. Drawing is not to scale.

Table 107. LQPF100 - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591

Using the values obtained in [Table 113](#) T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

$$T_{Jmax} = 100\text{ °C} + (45\text{ °C/W} \times 134\text{ mW}) = 100\text{ °C} + 6.03\text{ °C} = 106.03\text{ °C}$$

This is above the range of the suffix 6 version parts ($-40 < T_J < 105\text{ °C}$).

In this case, parts must be ordered at least with the temperature range suffix 7 (see [Section 8: Part numbering](#)) unless we reduce the power dissipation in order to be able to use suffix 6 parts.

Refer to [Figure 67](#) to select the required temperature range (suffix 6 or 7) according to your ambient temperature or power requirements.

Figure 67. LQFP64 P_D max vs. T_A

